

N-channel TrenchMOS logic level FET Rev. 02 — 7 June 2010

Product data sheet

Product profile 1.

1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant

- Suitable for logic level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

1.3 Applications

- 12 V loads
- Automotive systems

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- General purpose power switching
- Motors, lamps and solenoids

1.4 Quick reference data

| Table 1. | Quick reference | data | | | | | |
|------------------|----------------------------|--|------------|-----|-----|-----|------|
| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
| V_{DS} | drain-source voltage | T _j ≥ 25 °C; T _j ≤ 175 °C | | - | - | 40 | V |
| I _D | drain current | V _{GS} = 5 V; T _{mb} = 25 °C; see <u>Figure 1</u> ; see <u>Figure 3</u> | <u>[1]</u> | - | - | 75 | Α |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; see <u>Figure 2</u> | | - | - | 157 | W |
| Static cha | aracteristics | | | | | | |
| R_{DSon} | drain-source on-state | V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C | | - | 6.2 | 7 | mΩ |
| | resistance | $\label{eq:VGS} \begin{array}{l} V_{GS} = 5 \text{ V}; \text{ I}_D = 25 \text{ A}; \\ T_j = 25 \ ^\circ\text{C}; \\ \text{see } \underline{\text{Figure 11}}; \text{ see } \underline{\text{Figure 12}} \end{array}$ | | - | 7.6 | 9 | mΩ |

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| Table 1. | Quick reference da | tacontinued | | | | |
|-----------------|--|--|-----|-----|-----|------|
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
| Avalanch | e ruggedness | | | | | |
| $E_{DS(AL)S}$ | non-repetitive drain-source avalanche energy | $\begin{split} I_D &= 75 \text{ A}; V_{sup} \leq 40 \text{V}; \\ R_{GS} &= 50 \Omega; V_{GS} = 5 \text{V}; \\ T_{j(\text{init})} &= 25 ^\circ\text{C}; \text{ unclamped} \end{split}$ | - | - | 241 | mJ |
| Dynamic | characteristics | | | | | |
| Q _{GD} | gate-drain charge | $V_{GS} = 5 V; I_D = 25 A;$ $V_{DS} = 32 V; T_j = 25 °C;$ see Figure 13 | - | 12 | - | nC |

[1] Continuous current is limited by package.

2. Pinning information

| Table 2. | Pinning | information | | |
|----------|---------|-----------------------------------|--------------------|----------------|
| Pin | Symbol | Description | Simplified outline | Graphic symbol |
| 1 | G | gate | | - |
| 2 | D | drain ^[1] | mb | |
| 3 | S | source | | |
| mb | D | mounting base; connected to drain | | mbb076 S |
| | | | SOT404 (D2PAK) | |

[1] It is not possible to make a connection to pin 2.

3. Ordering information

Table 3.Ordering information

| Type number | Package | | |
|-------------|---------|--|---------|
| | Name | Description | Version |
| BUK9609-40B | D2PAK | plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped) | SOT404 |

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

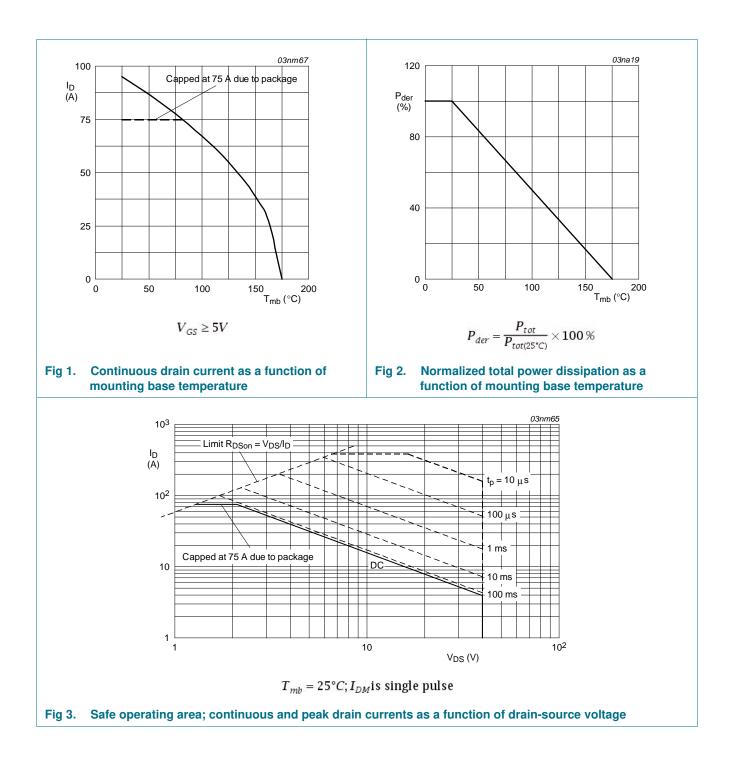
| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|----------------------|--|---|------------|-----|-----|-----|------|
| V _{DS} | drain-source voltage | T _j ≥ 25 °C; T _j ≤ 175 °C | | - | - | 40 | V |
| V _{DGR} | drain-gate voltage | $R_{GS} = 20 \text{ k}\Omega$ | | - | - | 40 | V |
| V _{GS} | gate-source voltage | | | -15 | - | 15 | V |
| I _D | drain current | T _{mb} = 25 °C; V _{GS} = 5 V; see <u>Figure 1;</u> see <u>Figure 3</u> | <u>[1]</u> | - | - | 95 | A |
| | | $T_{mb} = 100 \text{ °C}; V_{GS} = 5 \text{ V}; \text{ see } \frac{\text{Figure 1}}{\text{Figure 1}}$ | [1] | - | - | 67 | А |
| | | $T_{mb} = 25 \text{ °C}; V_{GS} = 5 \text{ V};$ see <u>Figure 1</u> ; see <u>Figure 3</u> | [2] | - | - | 75 | А |
| I _{DM} | peak drain current | T_{mb} = 25 °C; $t_p \le 10 \ \mu$ s; pulsed; see <u>Figure 3</u> | | - | - | 383 | A |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; see <u>Figure 2</u> | | - | - | 157 | W |
| T _{stg} | storage temperature | | | -55 | - | 175 | °C |
| Tj | junction temperature | | | -55 | - | 175 | °C |
| Source-drain | n diode | | | | | | |
| Is | source current | T _{mb} = 25 °C | <u>[1]</u> | - | - | 95 | А |
| | | | [2] | - | - | 75 | А |
| I _{SM} | peak source current | $t_p \le 10 \ \mu s$; pulsed; $T_{mb} = 25 \ ^{\circ}C$ | | - | - | 383 | А |
| Avalanche ru | uggedness | | | | | | |
| E _{DS(AL)S} | non-repetitive drain-source avalanche energy | $\label{eq:ID} \begin{array}{l} I_D = 75 \text{ A}; \ V_{sup} \leq 40 \text{ V}; \ R_{GS} = 50 \ \Omega; \\ V_{GS} = 5 \text{ V}; \ T_{j(\text{init})} = 25 \ ^\circ\text{C}; \ \text{unclamped} \end{array}$ | | - | - | 241 | mJ |

[1] Current is limited by power dissipation chip rating.

[2] Continuous current is limited by package.

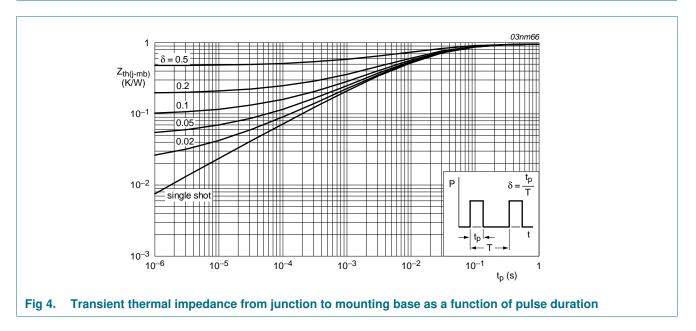
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5. Thermal characteristics

| Table 5. | Thermal characteristics | | | | | |
|-----------------------|---|--|-----|-----|------|------|
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
| $R_{\text{th(j-mb)}}$ | thermal resistance from junction to mounting base | see <u>Figure 4</u> | - | - | 0.95 | K/W |
| R _{th(j-a)} | thermal resistance from junction to ambient | minimum footprint ; mounted on a printed-circuit board | - | 50 | - | K/W |



6. Characteristics

| Table 6. | Characteristics | | | | | |
|--|---|---|-----|------|------|------|
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
| Static cha | racteristics | | | | | |
| V _{(BR)DSS} | drain-source | $I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$ | 36 | - | - | V |
| breakdown voltage | $I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$ | 40 | - | - | V | |
| V _{GS(th)} gate-source threshold voltage | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 10</u> | 1.1 | 1.5 | 2 | V | |
| | | I _D = 1 mA; V _{DS} = V _{GS} ; T _j = -55 °C; see <u>Figure 10</u> | - | - | 2.3 | V |
| | | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ see <u>Figure 10</u> | 0.5 | - | - | V |
| I _{DSS} | drain leakage current | $V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$ | - | 0.02 | 1 | μA |
| | | $V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$ | - | - | 500 | μA |
| I _{GSS} | gate leakage current | $V_{DS} = 0 \text{ V}; \text{ V}_{GS} = 15 \text{ V}; \text{ T}_{j} = 25 \text{ °C}$ | - | 2 | 100 | nA |
| | | $V_{DS} = 0 \text{ V}; \text{ V}_{GS} = -15 \text{ V}; \text{ T}_{j} = 25 \text{ °C}$ | - | 2 | 100 | nA |
| R _{DSon} | drain-source on-state | V_{GS} = 4.5 V; I _D = 25 A; T _j = 25 °C | - | - | 10 | mΩ |
| | resistance | V_{GS} = 10 V; I _D = 25 A; T _j = 25 °C | - | 6.2 | 7 | mΩ |
| | V _{GS} = 5 V; I _D = 25 A; T _j = 175 °C; see <u>Figure 11</u> ; see <u>Figure 12</u> | - | - | 17.1 | mΩ | |
| | | V _{GS} = 5 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 11</u> ; see <u>Figure 12</u> | - | 7.6 | 9 | mΩ |
| Dynamic (| characteristics | | | | | |
| Q _{G(tot)} | total gate charge | $I_D = 25 \text{ A}; V_{DS} = 32 \text{ V}; V_{GS} = 5 \text{ V};$ | - | 32 | - | nC |
| Q _{GS} | gate-source charge | $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 13}{13}$ | - | 7 | - | nC |
| Q _{GD} | gate-drain charge | | - | 12 | - | nC |
| C _{iss} | input capacitance | $V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;$ | - | 2700 | 3600 | pF |
| C _{oss} | output capacitance | T _j = 25 °C; see <u>Figure 14</u> | - | 450 | 540 | pF |
| C _{rss} | reverse transfer capacitance | | - | 207 | 283 | pF |
| t _{d(on)} | turn-on delay time | $V_{DS} = 30 \text{ V}; \text{ R}_{L} = 1.2 \Omega; V_{GS} = 5 \text{ V};$ $R_{G(ext)} = 10 \Omega; \text{ T}_{j} = 25 \text{ °C}$ | - | 29 | - | ns |
| t _r | rise time | $V_{DS} = 30 \text{ V}; \text{ R}_{L} = 1.2 \Omega; V_{GS} = 5 \text{ V};$ $R_{G(ext)} = 10 \Omega; \text{ T}_{j} 25 \text{ °C}$ | - | 106 | - | ns |
| d(off) | turn-off delay time | $V_{DS} = 30 \text{ V}; \text{ R}_{L} = 1.2 \Omega; \text{ V}_{GS} = 5 \text{ V};$ | - | 108 | - | ns |
| ^l f | fall time | $R_{G(ext)} = 10 \ \Omega; T_j = 25 \ ^{\circ}C$ | - | 89 | - | ns |
| L _D | internal drain inductance | from upper edge of drain mounting base to centre of die ; $T_j = 25 \text{ °C}$ | - | 2.5 | - | nH |
| | | from drain lead 6 mm from package to centre of die ; $T_j = 25 \text{ °C}$ | - | 4.5 | - | nH |
| L _S | internal source inductance | from source lead 6 mm from package to source bond pad ; $T_j = 25 \text{ °C}$ | - | 7.5 | - | nH |

Symbol

BUK9609-40B

Мах

Unit

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Тур

Min

| Source-dra | | | | | | |
|---|--|--|---|----------------------|-------------|--------|
| √ _{SD} | source-drain voltage | $I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C};$ see <u>Figure 15</u> | - | 0.85 | 1.2 | V |
| rr | reverse recovery time | $I_{S} = 20 \text{ A}; \text{ dI}_{S}/\text{dt} = -100 \text{ A}/\mu\text{s};$ | - | 57 | - | ns |
| ຸຊຸ | recovered charge | $V_{GS} = -10 \text{ V}; V_{DS} = 30 \text{ V}; T_j = 25 \text{ °C}$ | - | 47 | - | nC |
| 300 | 10 Label | 03nm62 1is V _{GS} (V) | | | 03nm61 | |
| I _D (A) | | R _{DSon} (mΩ) | | | | |
| 200 - | 4.8 4.6 4.4 4.4 4.2 | | | | | |
| 100 - | 4 3.8 3.6 | 8 | | | | |
| - | 3.4 3.2 3.2 3.2 2.8 2.8 2.4 | | | | | |
| 0 | | 8 10 3 V _{DS} (V) | 7 | 11 V _G | 15 S (V) | |
| | | | | | | |
| | $T_j = 25^{\circ}C; t_p = 300\mu$ | us | $T_j = 25^{\circ}C; I_D$ | = 25A | | |
| | $T_j = 25^{\circ}C; t_p = 300\mu$ putput characteristics: drain inction of drain-source volt | n current as a Fig 6. Drain-sou | $T_j = 25^{\circ}C; I_D$ since on-state repurce voltage; | esistanc | | unctio |
| | output characteristics: drain | n current as a Fig 6. Drain-sou | irce on-state re | esistanc | | unctio |
| fu | output characteristics: drain | Fig 6. Drain-sou age; typical values of gate-so | irce on-state re | esistanc | alues | unctio |
| 10 ⁻¹ I _D (A) | output characteristics: drain | Ourrent as a tage; typical values Fig 6. Drain-sour of gate-source 03ng53 9fs (S) 60 | irce on-state re | esistanc | alues | unctio |
| fu 10 ⁻¹ 10 (A) 10 ⁻² 10 ⁻³ | Putput characteristics: drain Inction of drain-source volt | Ourrent as a tage; typical values Fig 6. Drain-sour of gate-source 03ng53 9fs (S) 60 | irce on-state re | esistanc | alues | unctio |
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| fu 10 ⁻¹ 10 (A) 10 ⁻² 10 ⁻³ 10 ⁻⁴ 10 ⁻⁵ 10 ⁻⁶ | Putput characteristics: drain inction of drain-source volt | Fig 6. Drain-sou of gate-so of gate-so g_{fs} | purce on-state repurce voltage; | 40 ID | 03nm59 | |

Table 6. Characteristics ...continued

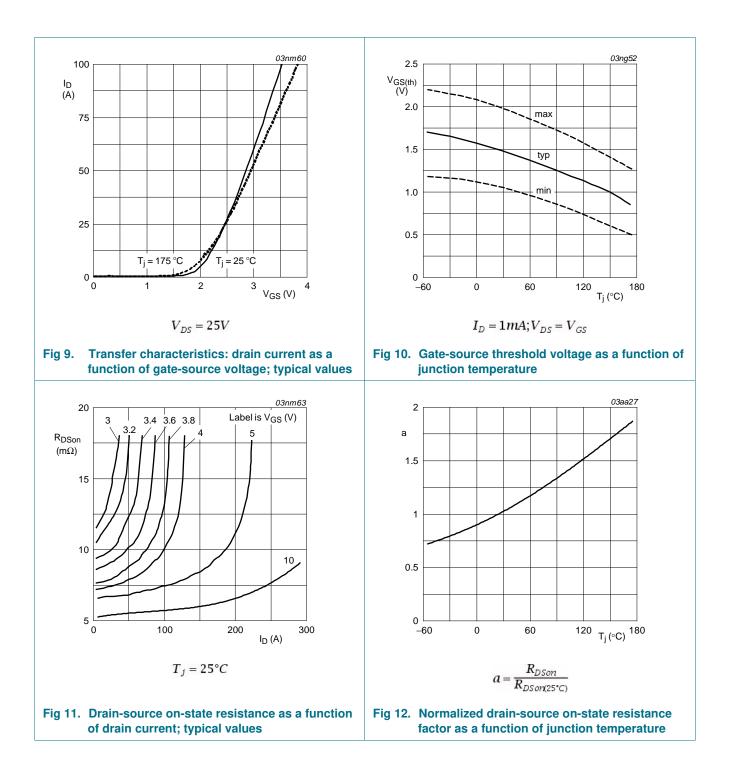
Parameter

Conditions

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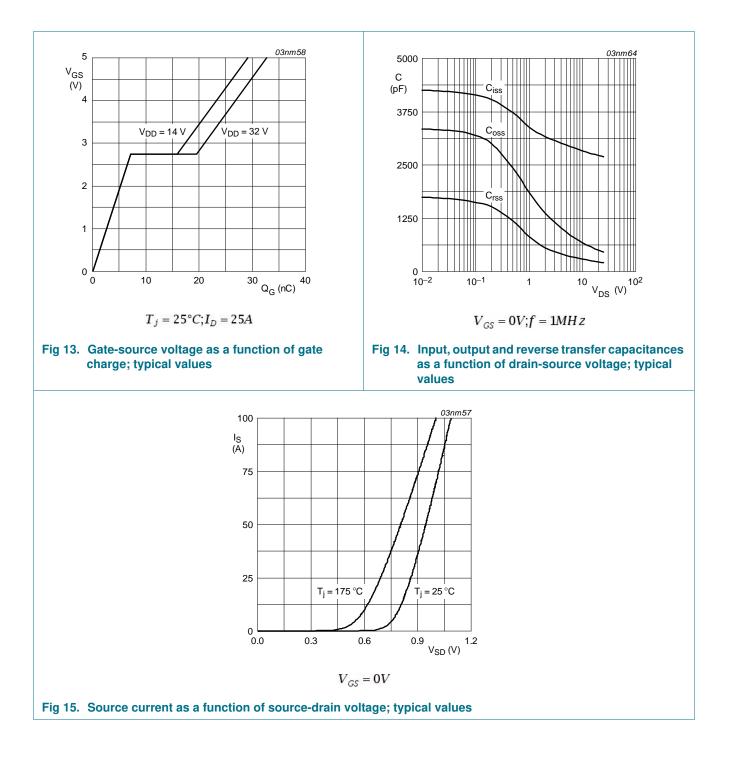
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7. Package outline

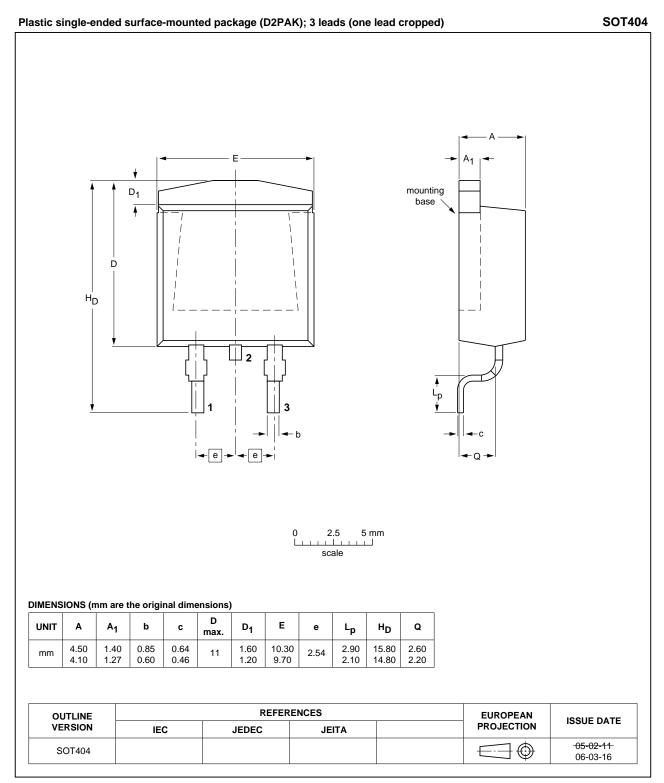


Fig 16. Package outline SOT404 (D2PAK)

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8. Revision history

| Table 7. Revision his | story | | | |
|-----------------------|---------------------------------|---|--------------------------|----------------------------------|
| Document ID | Release date | Data sheet status | Change notice | Supersedes |
| BUK9609-40B v.2 | 20100607 | Product data sheet | - | BUK95_9609_40B-01 |
| Modifications: | | t of this data sheet has be emiconductors. | en redesigned to comply | with the new identity guidelines |
| | Legal texts | s have been adapted to the | ne new company name w | nere appropriate. |
| | Type num | ber BUK9609-40B separa | ited from data sheet BUK | 95_9609_40B-01. |
| BUK95_9609_40B-01 | 20030415 | Product data | - | - |
| | | | | |

9. Legal information

9.1 Data sheet status

| Document status[1][2] | Product status ^[3] | Definition |
|--------------------------------|-------------------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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